## Carbon nanotubes as ultra-high quality factor mechanical resonators

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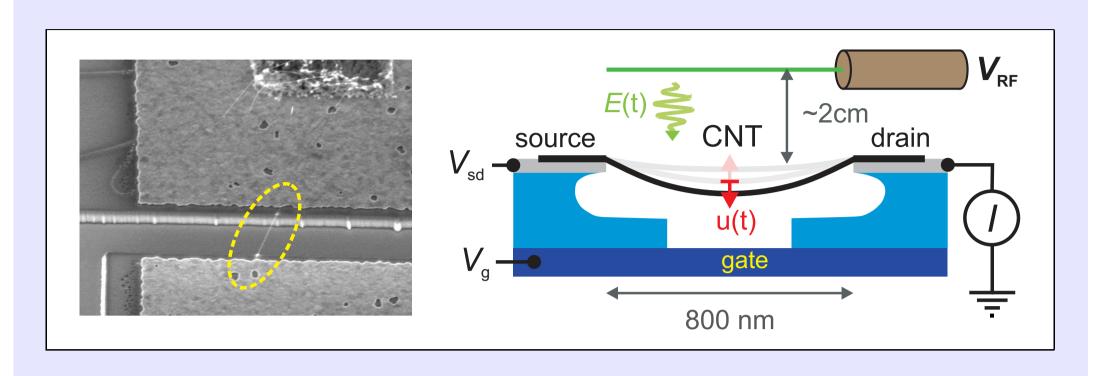


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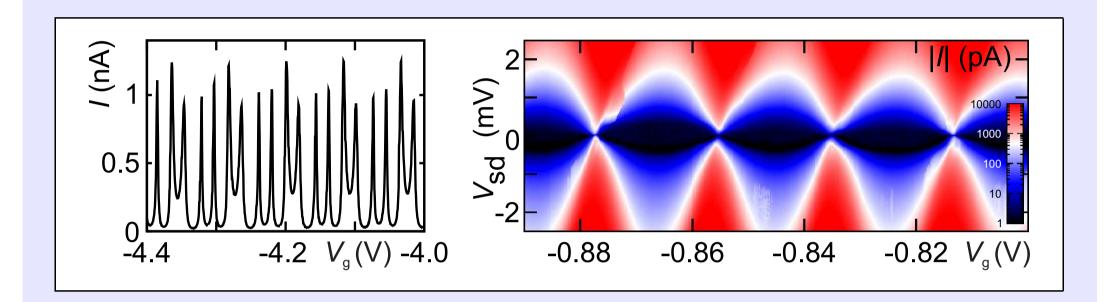




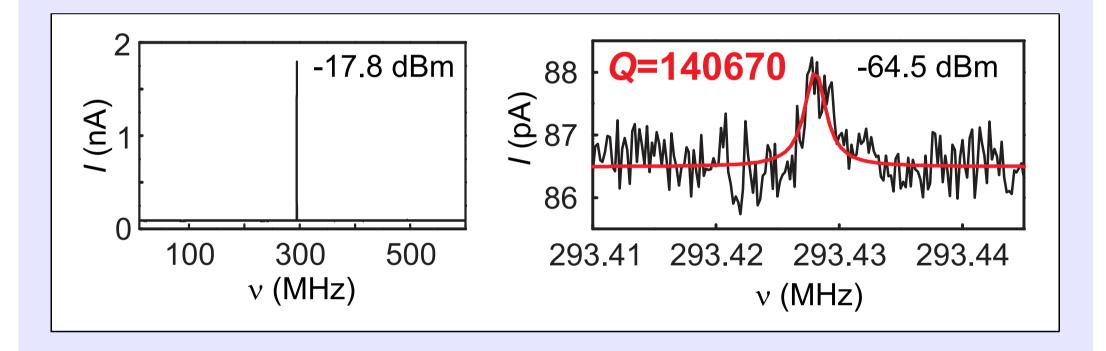
## Driving a CNT High-Q resonator



- p<sup>+</sup> doped Si wafer, SiO<sub>2</sub> layer on top
- Predefined trenches and Pt electrodes
- SW-CNT grown across structure [1]
- No further processing after growth

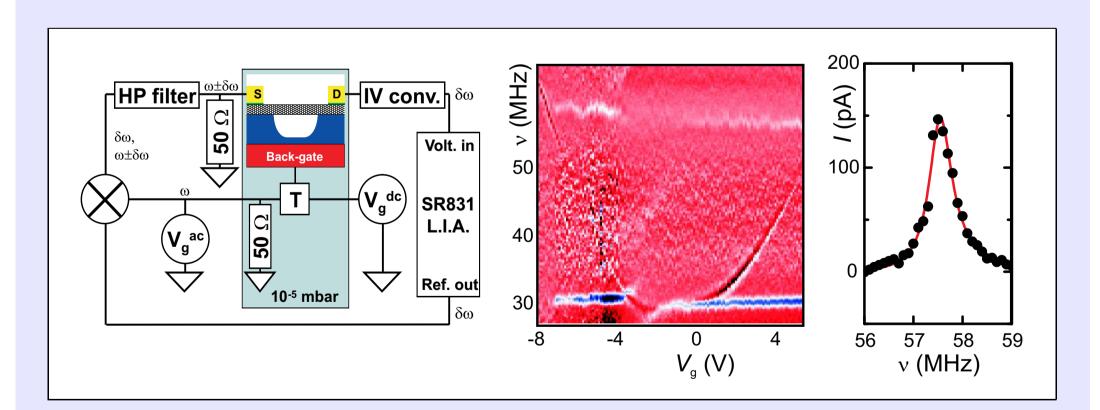


- Dilution refrigerator,  $T = 20 \,\mathrm{mK}$
- Highly regular quantum dot, 4-fold degeneracy, Kondo effect, electron and hole conductance



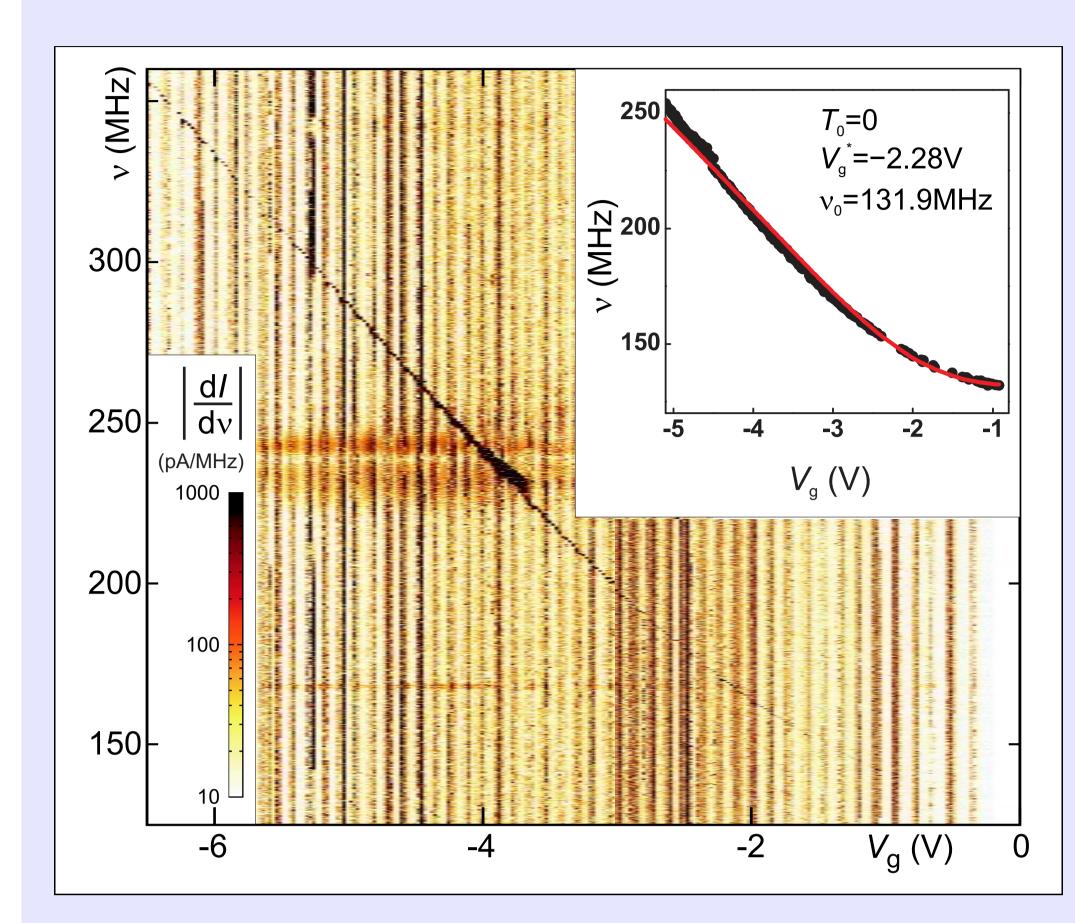
- Driving contact-free with RF signal [2]
- Mechanical resonance emerges as sharp feature in SET current
- We obtain mechanical quality factors  $Q \gtrsim 10^5$

### **Previous CNT resonators**



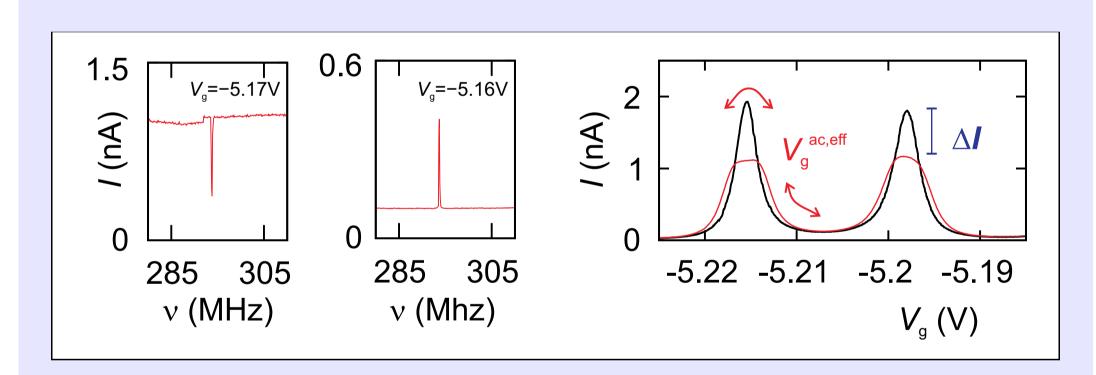
- Resonance detection by downmixing of a high-frequency signal [3, 4]
- Method developed for RT measurements
- Maximally observed:  $Q \sim 2000$  at T = 20 K [5]
- Driving signal applied directly at device & back gate
- → Two HF cables connected to sample
- → Heating, electromagnetic noise
- → Not good for very low temperature measurements

## Tuning the frequency by tension

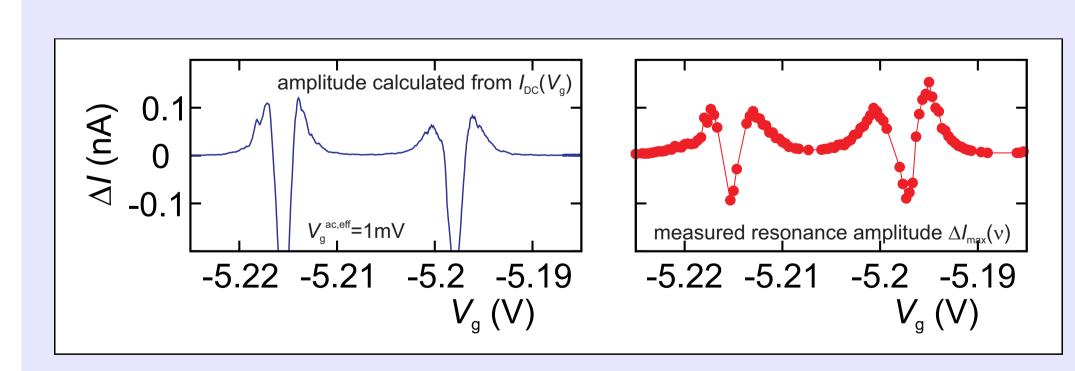


- Gate voltage induces tension in nanotube
- Characteristic  $v(V_g)$  of bending mode [4, 6]
- Good fit with continuum beam model
- Parameters consistent with CNT radius and length  $(r \simeq 1.5 \, \text{nm} \, \text{verified from} \, E_{\text{gap}} \, \text{and} \, \mu_{\text{orb}})$

## **Detection mechanism**



- Resonance in I(v) is peak or dip, depending on  $V_g$
- Driven motion  $u(t) = u_0 \cos(2\pi vt)$  geometrically modifies gate capacitance,  $C_g^{ac} = (dC_g/du) u_0$
- $C_{\rm g}^{\rm ac}$  acts equivalent to an  $V_{\rm g}^{\rm ac,eff} = V_{\rm g} C_{\rm g}^{\rm ac} / C_{\rm g}$
- CB oscillations are "smoothened out" at mechanical resonance



- Calculate expected  $\Delta I(V_{\rm g})$  from measured  $I_{\rm DC}(V_{\rm g})$
- Measure frequency traces  $I(v, V_g)$ , evaluate resonance amplitude  $\Delta I(V_g)$
- Good qualitative agreement
- Typical motion amplitude at resonance  $\sim 0.25\,\mathrm{nm}$

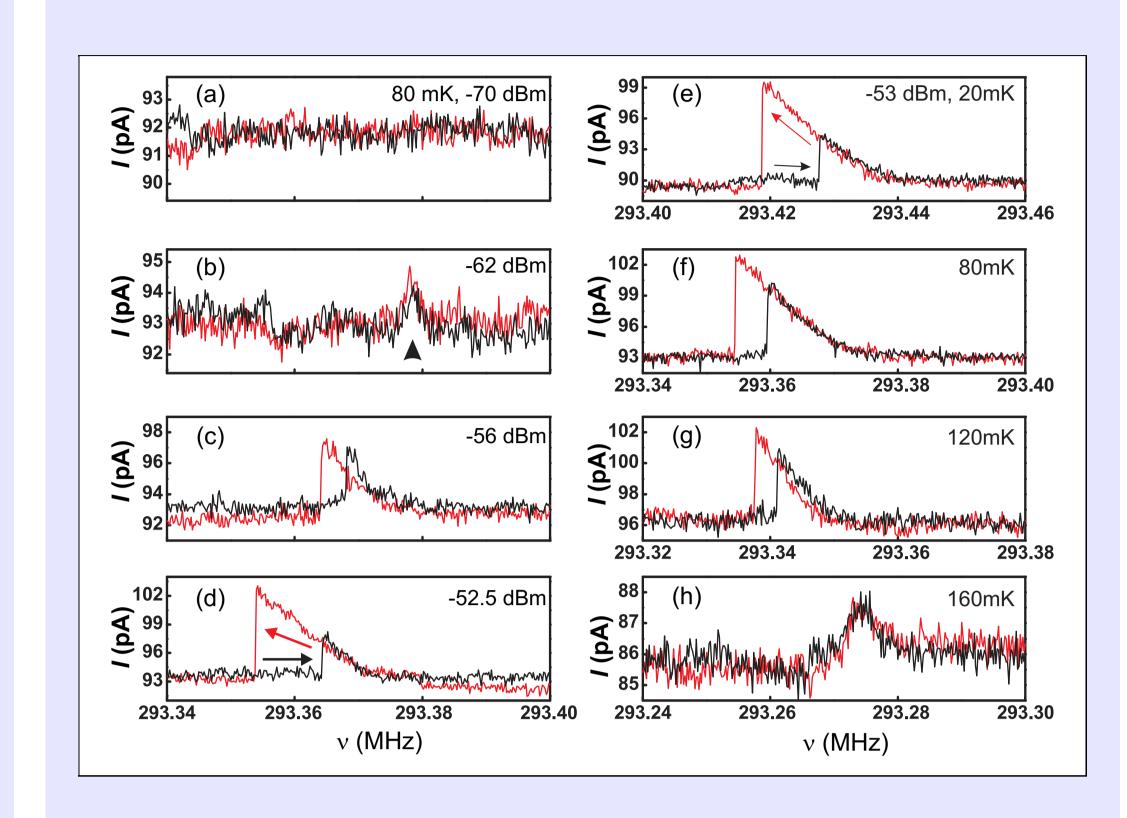
#### References

- [1] G. A. Steele et al., submitted for publication (2008).
- [2] A. K. Hüttel *et al.*, submitted for publication (2009).
- [3] V. Sazonova *et al.*, Nature **431**, 284 (2004).
- [4] B. Witkamp *et al.*, Nano Lett. **6**, 2904 (2006).
- [6] M. Poot et al., physica status solidi (b) 244, 4252 (2007).[7] H. W. C. Postma et al., Appl. Phys. Lett. 86, 223105 (2005).
- [5] B. Lassagne *et al.*, Nano Lett. **8**, 3735 (2008).
  [6] M. Poot *et al.* physica status solidi (b) **244** 4252 (2007).

[8] H. Jiang et al., Phys. Rev. Lett. 93, 185501 (2004).

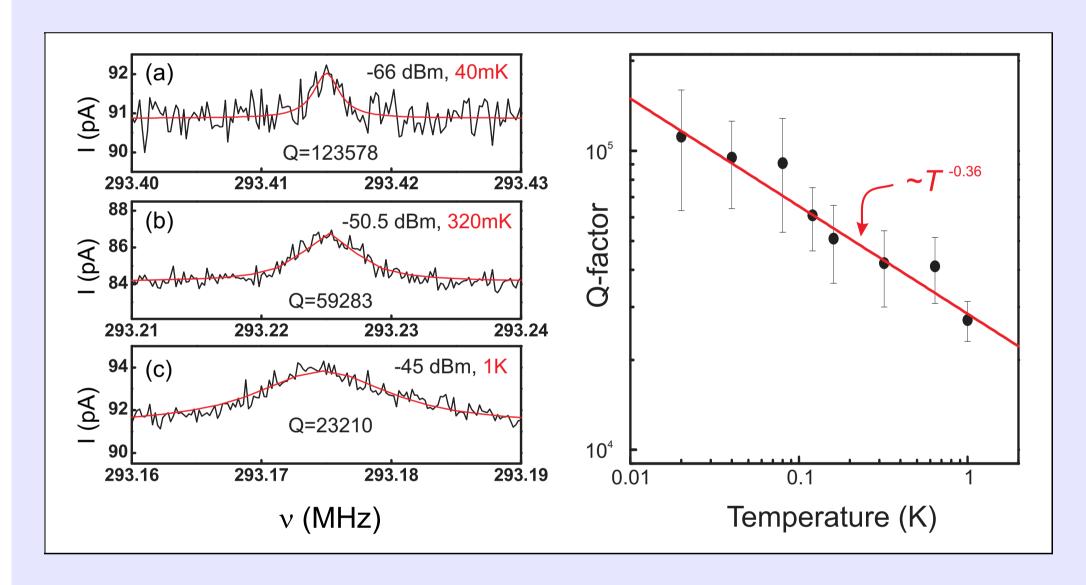
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## Driving into the nonlinear regime



- Power range for linear response very small [7]
- Nonlinear oscillator at strong driving
- Hysteretic behaviour, frequency pulling
- Linear behaviour is restored by temperature increase

## The ultimate Q limit



- Molecular dynamics calculations [8] predict an intrinsic  $Q \sim 10^5$
- This is what we reach at base temperature
- Q decreases significantly at higher temperature
- Calculations predict  $Q \propto T^{-0.36}$ , agree beautifully

### Outlook

• Frequency  $v = 355 \, \text{MHz}$ , temperature  $T_{\text{MC}} = 20 \, \text{mK}$ — mechanical mode thermal occupation

$$n = \frac{1}{2} + \left[ \exp\left(\frac{hv_0}{k_{\rm B}T_{\rm MC}}\right) - 1 \right]^{-1} = 1.2$$

Quantum-mechanical oscillator!

• High Q, frequency depends on resonator mass  $\longrightarrow$  mass sensitivity

$$\sqrt{S_m} = \frac{\partial m}{\partial v_0} \left(\frac{\partial I}{\partial v}\right)^{-1} \sqrt{S_I} = 7.0 \frac{\text{yg}}{\sqrt{\text{Hz}}} \simeq 4 \frac{\text{u}}{\sqrt{\text{Hz}}}$$

Detect adsorbed He atom in 1s!

• Shorter devices with higher resonance frequency easily possible!